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(54) **METHOD FOR MANUFACTURING BONDED
WAFER, AND BONDED WAFER**

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ABSTRACT

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A method for manufacturing a bonded wafer, the method including bonding a to-be-bonded wafer and a compound semiconductor wafer including a compound semiconductor epitaxially grown on a growth substrate. An area of a bonding surface of the to-be-bonded wafer is larger than an area of a bonding surface of the compound semiconductor wafer. The growth substrate is removed after the to-be-bonded wafer is bonded to the compound semiconductor wafer.

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110

